

THE INFLUENCE OF AlGaAs/GaAs HBT'S STRUCTURAL PARAMETERS AND BIAS POINT ON NONLINEAR CHARACTERISTICS OF INPUT AMPLIFIERS

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The influence of electro-physical, geometrical parameters and bias point of AlGaAs/GaAs hetero-junction bipolar transistor on its blocking dynamic range was investigated. Also the change of gain was considered. Using this investigation the method of parameter's choice was suggested for improvement of electromagnetic compatibility's characteristics of hetero-junction bipolar transistor amplifiers.